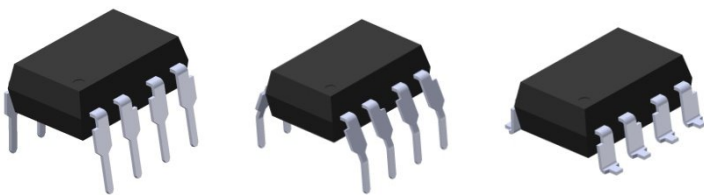
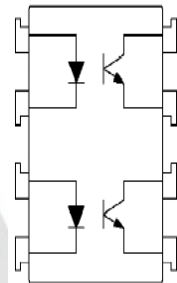


8 PIN DIP PHOTOTRANSISTOR PHOTOCOUPLER EL827 Series



Schematic



Pin Configuration

- 1, 3. Anode
- 2, 4. Cathode
- 5, 7. Emitter
- 6, 8. Collector

Features:

- Current transfer ratio
(CTR: 50~600% at $I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
- High isolation voltage between input and output (Viso=5000 V rms)
- Compact small outline package
- Pb free and RoHS compliant.
- UL and cUL approved(No. E214129)
- VDE approved (No. 132249)
- SEMKO approved
- NEMKO approved
- DEMKO approved
- FIMKO approved
- CQC approved

Description

The EL827series devices each of consist of an infrared emitting diodes, optically coupled to a phototransistor detector. They are packaged in a 8-pin DIP package and available in wide-lead spacing and SMD option.

Applications

- Programmable controllers
- System appliances, measuring instruments
- Telecommunication equipments
- Home appliances, such as fan heaters, etc.
- Signal transmission between circuits of different potentials and impedances

Absolute Maximum Ratings (Ta=25 °C)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I _F	60	mA
	Peak forward current (1us, pulse)	I _{FP}	1	A
	Reverse voltage	V _R	6	V
	Power dissipation	P _D	100	mW
Output	Power dissipation	P _C	150	mW
	Collector current	I _C	50	mA
	Collector-Emitter voltage	V _{CEO}	80	V
	Emitter-Collector voltage	V _{ECO}	7	V
	Total power dissipation	P _{TOT}	200	mW
	Isolation voltage ^{*1}	V _{ISO}	5000	V rms
	Operating temperature	T _{OPR}	-55 to 110	°C
	Storage temperature	T _{STG}	-55 to 125	°C
	Soldering temperature ^{*2}	T _{SOL}	260	°C

Notes:

*1 AC for 1 minute, R.H.= 40 ~ 60% R.H. In this test, pins 1, 2 & 3, 4 are shorted together, and pins 5, 6 & 7, 8 are shorted together.

*2 For 10 seconds

Electro-Optical Characteristics (Ta=25 unless specified otherwise)

Input

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Forward Voltage	V_F	-	1.2	1.4	V	$I_F = 20\text{mA}$
Reverse Current	I_R	-	-	10	μA	$V_R = 4\text{V}$
Input capacitance	C_{in}	-	30	250	pF	$V = 0, f = 1\text{kHz}$

Output

Parameter	Symbol	Min.	Typ.*	Max.	Unit	Condition
Collector-Emitter dark current	I_{CEO}	-	-	100	nA	$V_{CE} = 20\text{V}, I_F = 0\text{mA}$
Collector-Emitter breakdown voltage	BV_{CEO}	80	-	-	V	$I_C = 0.1\text{mA}$
Emitter-Collector breakdown voltage	BV_{ECO}	7	-	-	V	$I_E = 0.1\text{mA}$

Transfer Characteristics

Parameter	Symbol	Min	Typ.	Max.	Unit	Condition
Current Transfer ratio	CTR	50	-	600	%	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$
Collector-Emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.2	V	$I_F = 20\text{mA}, I_C = 1\text{mA}$
Isolation resistance	R_{IO}	5×10^{10}	-	-	Ω	$V_{IO} = 500\text{Vdc}, 40\sim 60\% \text{ R.H.}$
Floating capacitance	C_{IO}	-	0.6	1.0	pF	$V_{IO} = 0, f = 1\text{MHz}$
Cut-off frequency	fc	-	80	-	kHz	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$ $R_L = 100\Omega, -3\text{dB}$
Rise time	t_r	-	3	18	μs	$V_{CE} = 2\text{V}, I_C = 2\text{mA},$ $R_L = 100\Omega$
Fall time	t_f	-	4	18	μs	$R_L = 100\Omega$

* Typical values at $T_a = 25^\circ\text{C}$

Typical Electro-Optical Characteristics Curves

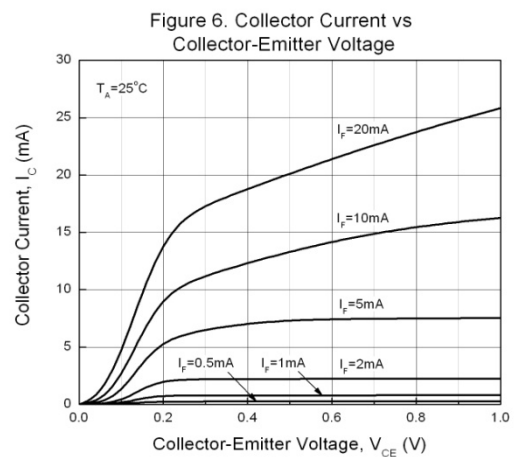
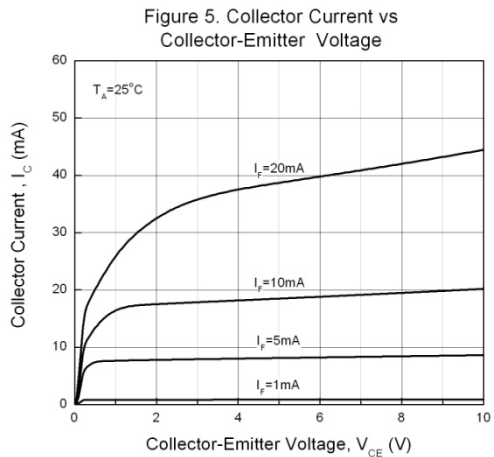
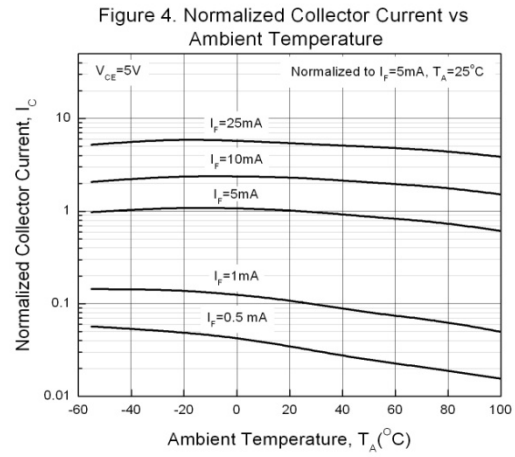
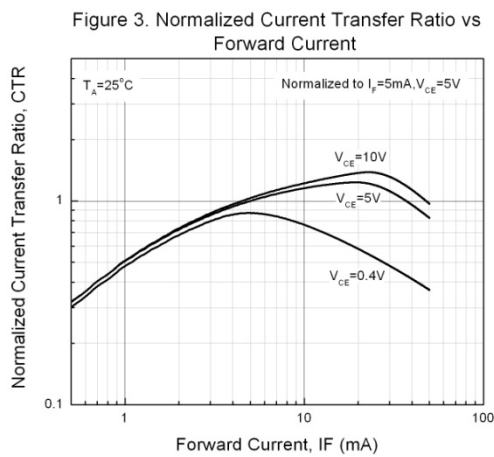
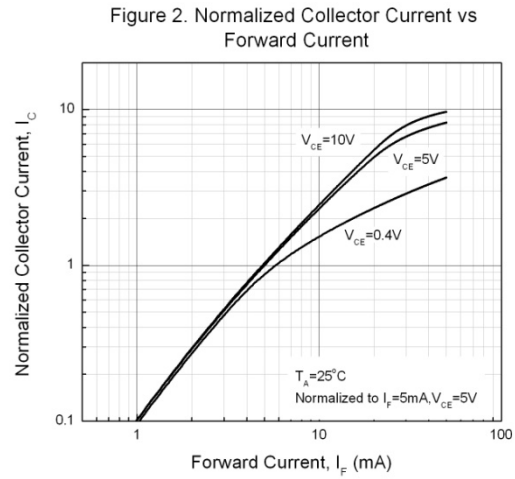
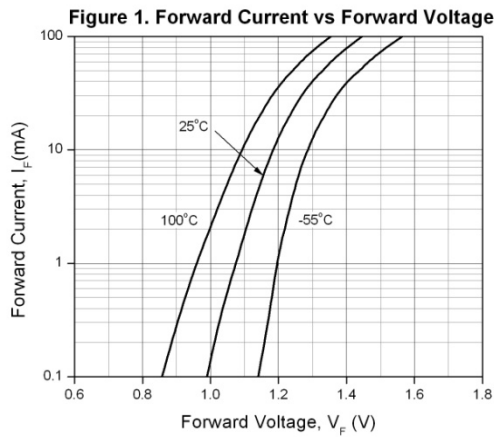


Figure 7. Collector Dark Current vs Ambient Temperature

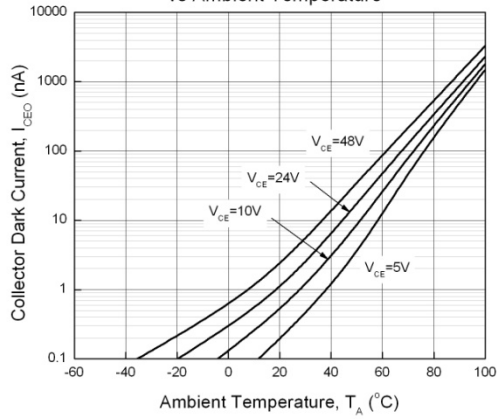


Figure 8. Switching Time vs Load Resistance

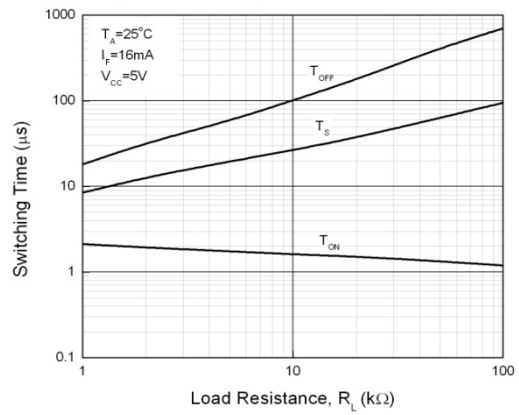


Figure 9. Collector-Emitter Saturation Voltage vs Ambient Temperature

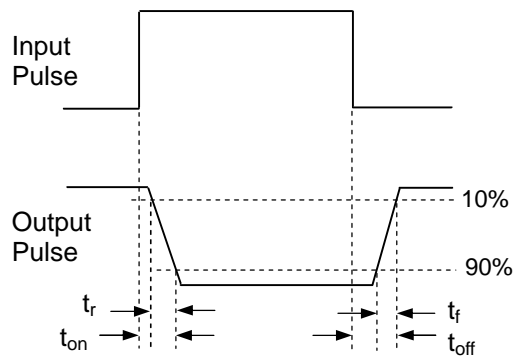
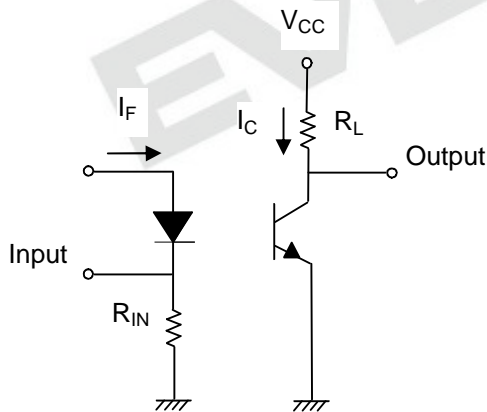
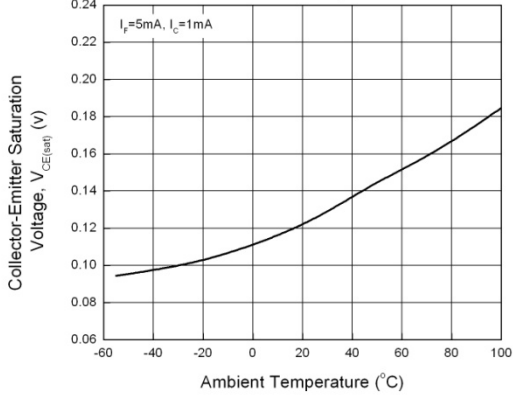


Figure 10. Switching Time Test Circuit & Waveforms

Order Information

Part Number

EL827X(Z)-V

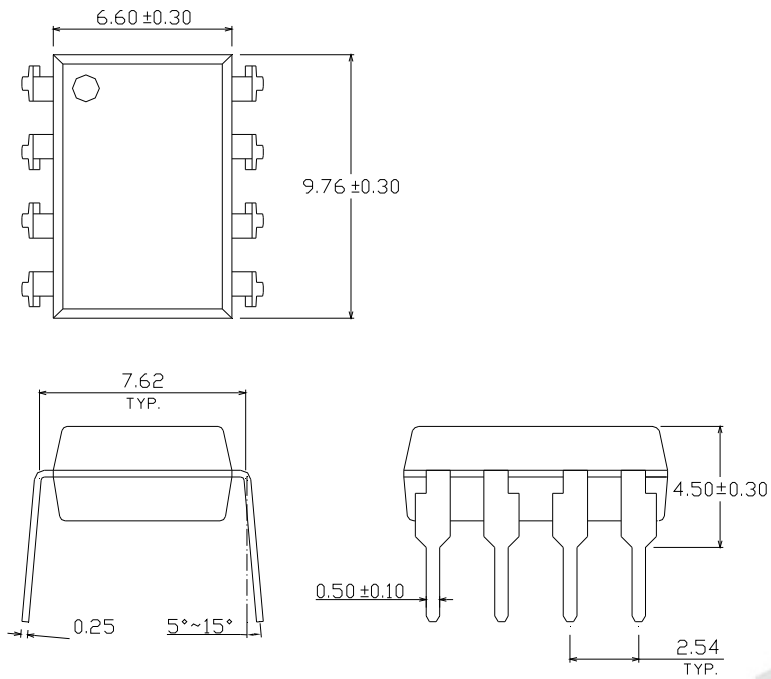
Note

- X = Lead form option (S, S1, M or none)
- Z = Tape and reel option (TA, TB or none)
- V = VDE safety (optional)

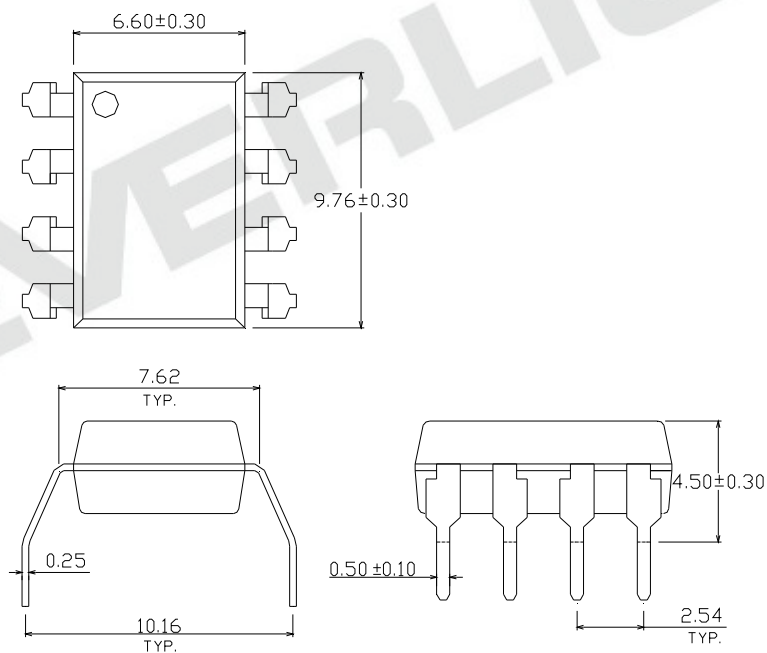
Option	Description	Packing quantity
None	Standard DIP-8	45 units per tube
M	Wide lead bend (0.4 inch spacing)	45 units per tube
S (TA)	Surface mount lead form + TA tape & reel option	1000 units per reel
S (TB)	Surface mount lead form + TB tape & reel option	1000 units per reel
S1 (TA)	Surface mount lead form (low profile) + TA tape & reel option	1000 units per reel
S1 (TB)	Surface mount lead form (low profile) + TB tape & reel option	1000 units per reel

Package Dimension (Dimensions in mm)

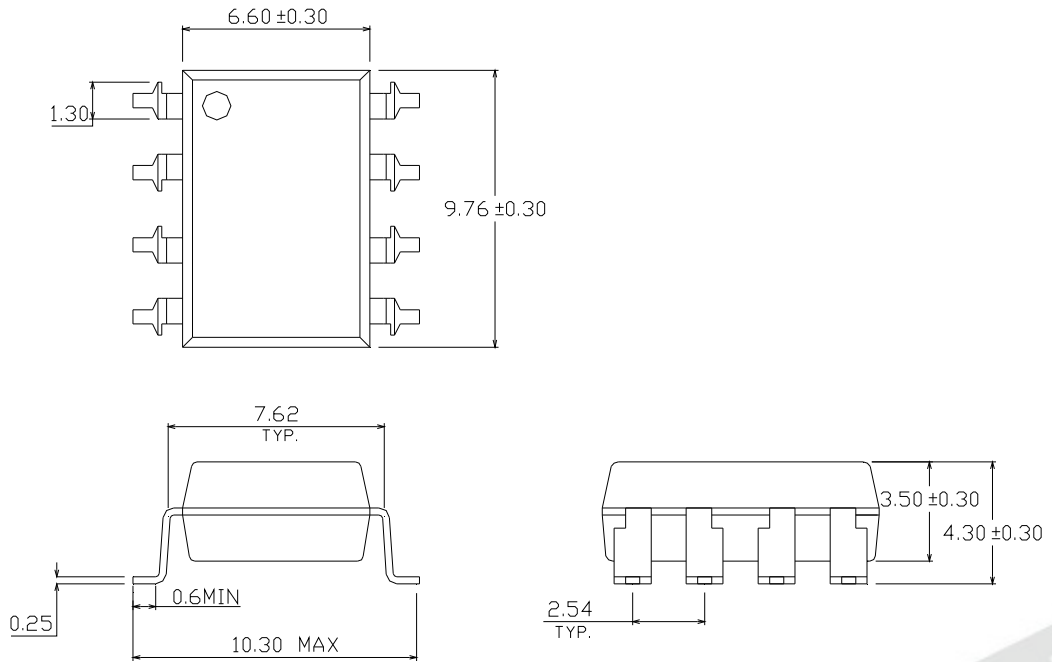
Standard DIP Type



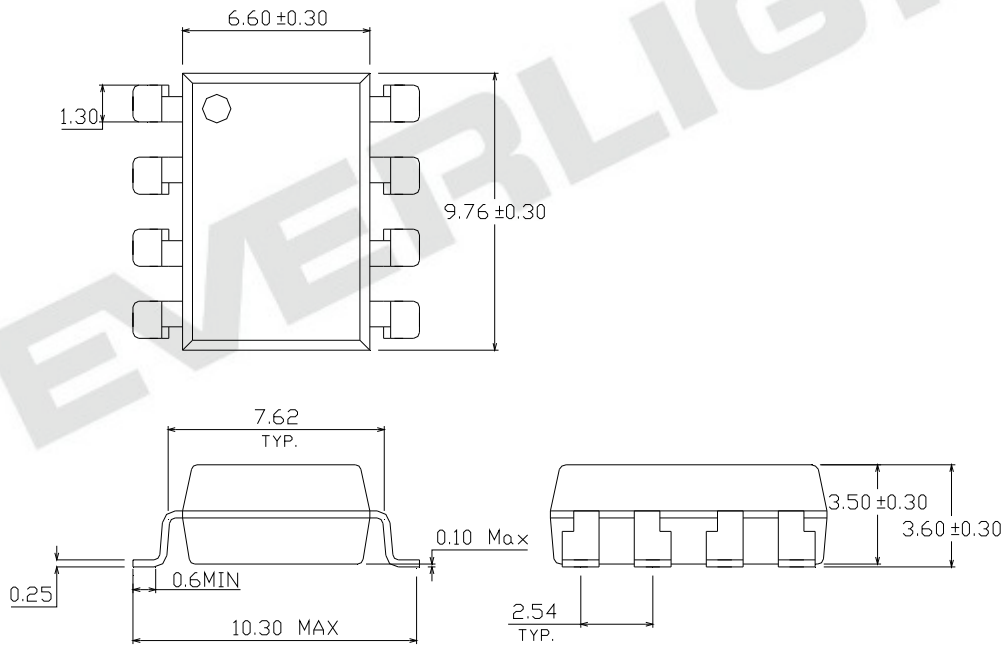
Option M Type



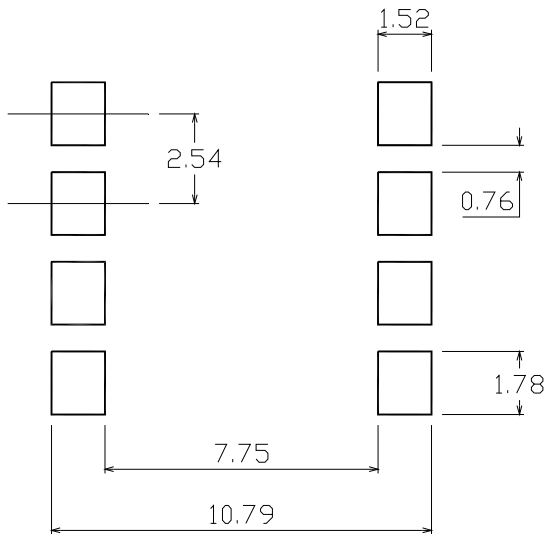
Option S Type



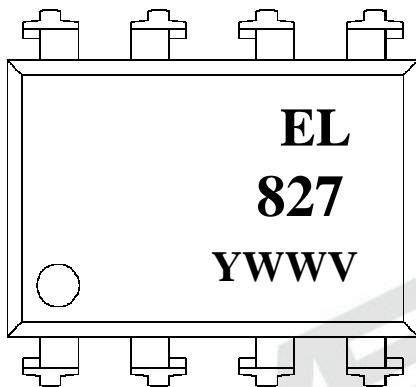
Option S1 Type



Recommended pad layout for surface mount leadform



Device Marking

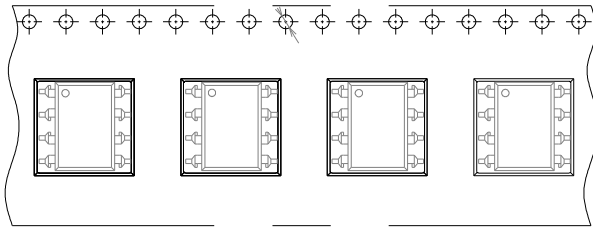


Notes

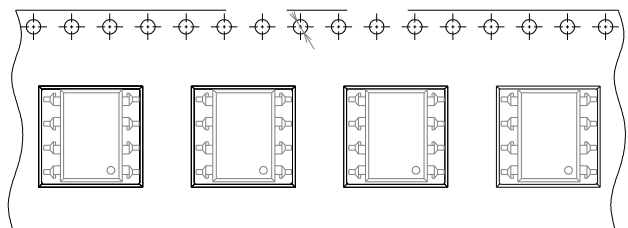
- EL827 denotes Device Number
- Y denotes 1 digit Year code
- WW denotes 2 digit Week code
- V denotes VDE (optional)

Tape & Reel Packing Specifications

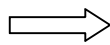
Option TA



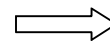
Option TB



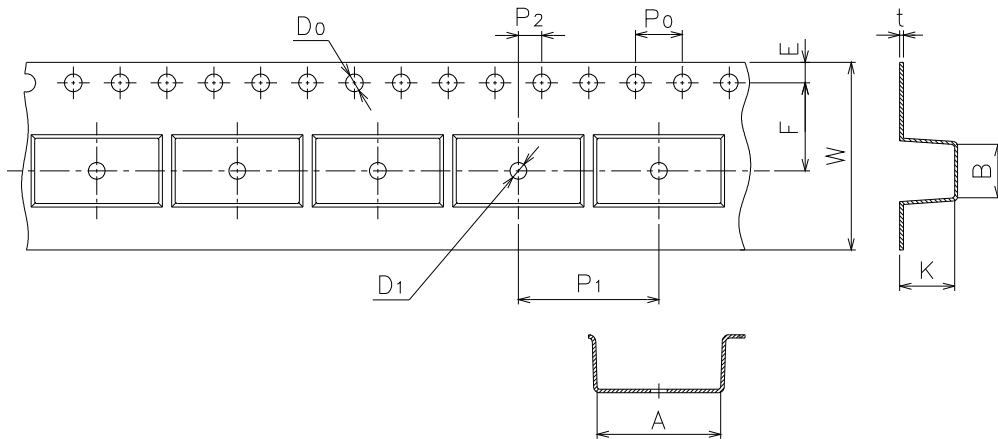
Direction of feed from reel



Direction of feed from reel



Tape dimensions

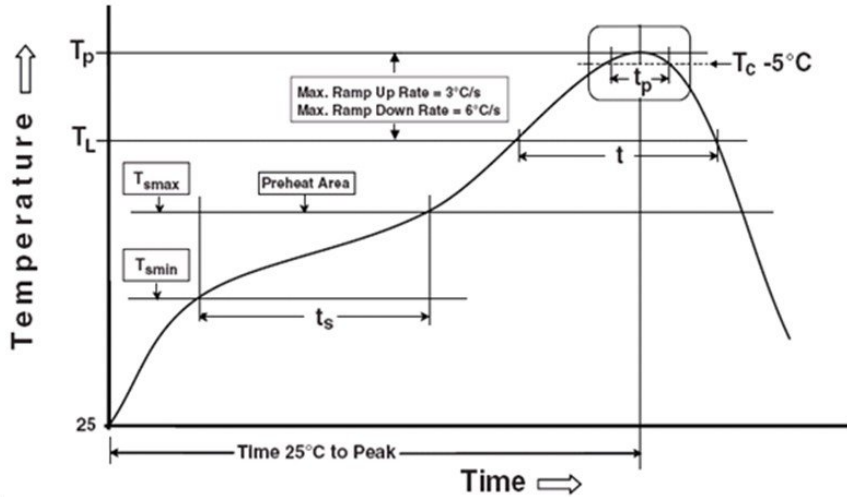


Dimension No.	A	B	Do	D1	E	F
Dimension(mm)	10.4±0.1	10.0±0.1	1.5±0.1	1.5+0.25 -0.1	1.75±0.1	7.5±0.1
Dimension No.	Po	P1	P2	t	W	K
Dimension(mm)	4.0±0.1	12.0±0.1	2.0±0.1	0.4±0.1	16.0±0.3	4.5±0.1

Precautions for Use

1. Soldering Condition

1.1 (A) Maximum Body Case Temperature Profile for evaluation of Reflow Profile



Note:

Reference: IPC/JEDEC J-STD-020D

Preheat

Temperature min (T_{smin})	150 °C
Temperature max (T_{smax})	200°C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max

Other

Liquidus Temperature (T_L)	217 °C
Time above Liquidus Temperature (t_L)	60-100 sec
Peak Temperature (T_p)	260°C
Time within 5 °C of Actual Peak Temperature: $T_p - 5^\circ\text{C}$	30 s
Ramp- Down Rate from Peak Temperature	6°C /second max.
Time 25°C to peak temperature	8 minutes max.
Reflow times	3 times